

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1838	((back or bottom) near3 gate) and (soi or (silicon adj on adj insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:04
L2	227	L1 and lithographic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:04
L3	33	L1 and ((sub near2 lithographic) or sublithographic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:28
L4	157	(soi or (silicon adj on adj insulator)) and ((sub near2 lithographic) or sublithographic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:04
L5	124	L4 not L3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:04
L6	227	2 not L5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:05
L7	2604	257/347.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:27
L8	414	257/352.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:27
L9	1365	438/149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:27

L10	2248	257/774.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:27
L11	1019	438/479.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:28
L12	217	438/517.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:28
L13	7241	7 8 9 10 11 12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:28
L14	343	13 and lithographic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:28
L15	348	13 and ((sub near2 lithographic) or sublithographic or lithographic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:29
L16	317	14 not 6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:29
L17	298	16 not 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:29
L18	298	17 not 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:29
S1	1595	257/774.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:27

S2	18	channel SAME (trench near10 (body adj contact))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 13:10
S3	100	(trench near10 (body adj contact))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 13:29
S4	5486	double near3 gate\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 13:30
S5	370	(double near3 gate\$1) and sidewalls	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 13:33
S6	123	((double near3 gate\$1) and sidewalls) and (soi or (silicon adj on adj insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 15:06
S7	21145	(back or bottom) near3 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 15:08
S8	1059	((back or bottom) near3 gate) and (soi or (silicon adj on adj insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/28 12:59
S9	417	(((back or bottom) near3 gate) and (soi or (silicon adj on adj insulator))) and sidewall\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/18 10:36
S10	344	(((back or bottom) near3 gate) and (soi or (silicon adj on adj insulator))) and sidewall\$1) not (((double near3 gate\$1) and sidewalls) and (soi or (silicon adj on adj insulator)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 15:07
S11	557	((back or bottom) near3 gate) with trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 15:09

S12	86	((back or bottom) near3 gate) with trench) and (soi or (silicon adj on adj insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 15:30
S13	70	(((back or bottom) near3 gate) with trench) and (soi or (silicon adj on adj insulator))) not (((double near3 gate\$1) and sidewalls) and (soi or (silicon adj on adj insulator)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 16:35
S14	1812	257/347.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/09 16:37
S15	1	("6597036").PN.	USPAT; USOCR	OR	OFF	2004/01/12 00:05
S16	38	((back or bottom) near3 gate) and (si or silicon) and (dielectric or oxide or insulator) and ((lithographic or sub-lithographic or sublithographic) near3 width) and (sidewalls)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 00:33
S17	44	((back or bottom) near3 gate) and (si or silicon) and (dielectric or oxide or insulator) and ((lithographic or sub-lithographic or sublithographic) near3 width)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 00:38
S18	6	(((back or bottom) near3 gate) and (si or silicon) and (dielectric or oxide or insulator) and ((lithographic or sub-lithographic or sublithographic) near3 width) ) not (((back or bottom) near3 gate) and (si or silicon) and (dielectric or oxide or insulator) and ((lithographic or sub-lithographic or sublithographic) near3 width) and (sidewalls))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 00:33
S19	0	(((back or bottom) adj gate) and ((lithographic or sub-lithographic or sublithographic) near3 width) ) not (((back or bottom) near3 gate) and (si or silicon) and (dielectric or oxide or insulator) and ((lithographic or sub-lithographic or sublithographic) near3 width) )	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 00:37

S20	19	((back or bottom) adj gate) and ((lithographic or sub-lithographic or sublithographic) near3 width)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 00:39
S21	2033	257/347.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:27
S22	377	257/352.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 00:39
S23	898	438/149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:27
S24	0	438/1479.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 00:39
S25	871	438/479.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:28
S26	167	438/517.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:28
S27	280	((back or bottom) adj gate) and (lithographic or sub-lithographic or sublithographic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 00:40
S28	261	((back or bottom) adj gate) and (lithographic or sub-lithographic or sublithographic) ) not ((back or bottom) near3 gate) and (si or silicon) and (dielectric or oxide or insulator) and ((lithographic or sub-lithographic or sublithographic) near3 width) )	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 09:37

S29	8626	((back or bottom) adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 09:43
S30	1590	(((back or bottom) adj gate) ) and ((2003-656296.NRAN, and (((back or bottom) adj gate) and (lithographic or sub-lithographic or sublithographic) ) not (((back or bottom) near3 gate) and (si or silicon) and (dielectric or oxide or insulator) and ((lithographic or sub-lithographic or sublithographic) near3 width) ))) nm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 09:42
S31	0	((back or bottom) adj gate) WITH (60nm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 09:44
S32	0	((back or bottom) adj gate) same (60nm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/12 09:46
S33	1	("6580132").PN.	USPAT; USOCR	OR	OFF	2004/01/12 13:05
S34	0	("10339844").PN.	USPAT; USOCR	OR	OFF	2004/01/12 13:06
S35	1	("6331733").PN.	USPAT; USOCR	OR	OFF	2004/01/12 13:06
S36	1	("6043535").PN.	USPAT	OR	OFF	2005/02/18 10:34
S37	1	("20020086465").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/18 10:34
S38	729	(((back or bottom) near3 gate) and (soi or (silicon adj on adj insulator))) and sidewall\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/18 12:21
S39	176	(semiconductor or ic or die or chip or (integrated adj circuit)) and (gate WITH (sub-lithographic or (sub near2 lithographic) or sublithographic))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/18 12:23

S40	34	(US-20020030282-\$ or US-20020036353-\$ or US-20020063110-\$ or US-20020079588-\$ or US-20020084488-\$ or US-20020084533-\$ or US-20020086465-\$ or US-20020094619-\$ or US-20020105039-\$ or US-20020130421-\$ or US-20020171105-\$ or US-20020177263-\$ or US-20030001240-\$ or US-20030025157-\$ or US-20030075730-\$ or US-20040180484-\$).did. or (US-5610083-\$ or US-5773331-\$ or US-5963818-\$ or US-6004837-\$ or US-6043535-\$ or US-6064589-\$ or US-6211533-\$ or US-6342717-\$ or US-6383904-\$ or US-6391695-\$ or US-6538916-\$ or US-6597036-\$ or US-6750494-\$).did. or (JP-05183163-\$ or JP-08162640-\$).did. or (US-5773331-\$ or US-6372559-\$ or US-6580132-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/02/22 10:26
S41	3	S40 and (sublithographic)	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/02/22 10:29
S42	5	S40 and (sub near2 lithographic)	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/02/22 10:31
S43	1	("6759315").PN.	USPAT	OR	OFF	2005/02/22 10:31
S44	1838	((back or bottom) near3 gate) and (soi or (silicon adj on adj insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/29 15:04
S45	33	S44 and ((sub near2 lithographic) or sublithographic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/28 13:01
S46	157	(soi or (silicon adj on adj insulator)) and ((sub near2 lithographic) or sublithographic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/28 13:16

S47	124	S46 not S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/28 13:16
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